**ON Semiconductor** 

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# Onsemi

To learn more about onsemi<sup>™</sup>, please visit our website at <u>www.onsemi.com</u>

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# Silicon Carbide Schottky Diode

650 V, 30 A

# FFSH3065A

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size & cost.

#### Features

- Max Junction Temperature 175°C
- Avalanche Rated 180 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery / No Forward Recovery
- This Device is Pb-Free and is RoHS Compliant

#### Applications

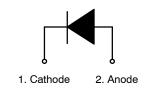
- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits



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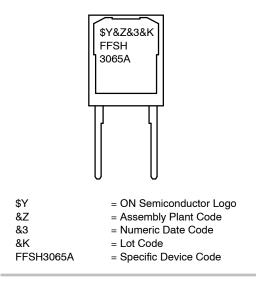
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V <sub>RRM</sub>	IF	
650 V	30 A	





#### MARKING DIAGRAM



#### **ORDERING INFORMATION**

See detailed ordering and shipping information on page 2 of this data sheet.

#### ABSOLUTE MAXIMUM RATINGS (T<sub>C</sub> = 25°C, Unless otherwise specified)

Symbol	Parameter		FFSH3065A	Unit
V <sub>RRM</sub>	Peak Repetitive Reverse Voltage		650	V
E <sub>AS</sub>	Single Pulse Avalanche Energy (Note 1)		180	mJ
١ <sub>F</sub>	Continuous Rectified Forward Current @ Tc < 145°C		30	А
		@ Tc < 135°C	36	
I <sub>F, Max</sub>	Max Non-Repetitive Peak Forward Surge Current	Tc = 25°C, 10 μs	1125	A
		Tc = 150°C, 10 μs	1040	A
I <sub>F, SM</sub>	Non-Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	150	А
I <sub>F, RM</sub>	Repetitive Forward Surge Current	Half-Sine Pulse, tp = 8.3 ms	75	А
P <sub>tot</sub> Power Dissipation		Tc = 25°C	259	W
		Tc = 150°C	43	W
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		–55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1.  $E_{AS}$  of 180 mJ is based on starting  $T_J = 25^{\circ}C$ , L = 0.5 mH,  $I_{AS} = 27$  A, V = 50 V.

#### **THERMAL CHARACTERISTICS**

Symbol	Parameter	Rating	Unit	
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.58	°C/W	

#### PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH3065A	FFSH3065A	TO247-2L	Tube	N/A	N/A	30 Units

#### **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	Forward Voltage	IF = 30 A, Tc = 25°C	-	1.50	1.75	V
		IF = 30 A, Tc = 125°C	-	1.60	2.0	
		IF = 30 A, Tc = 175°C	-	1.72	2.4	
I <sub>R</sub>	Reverse Current	VR = 650 V, Tc = 25°C	-	-	200	μA
		VR = 650 V, Tc = 125°C	-	-	400	
		VR = 650 V, Tc = 175°C	-	-	600	
Q <sub>C</sub>	Total Capacitive Charge	V = 400 V	-	100	-	nC
С	Total Capacitance	VR = 1 V, f = 100 kHz	-	1705	-	pF
		VR = 200 V, f = 100 kHz	-	180	-	
		V <sub>R</sub> = 400 V, f = 100 kHz	-	130	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## **TYPICAL CHARACTERISTICS**

(T<sub>J</sub> = 25°C unless otherwise noted)

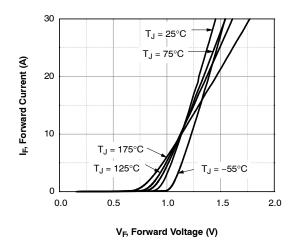
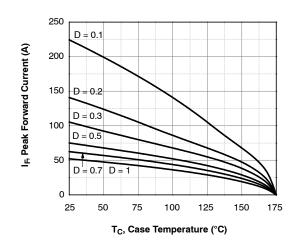
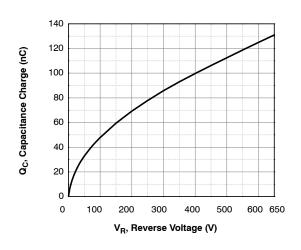


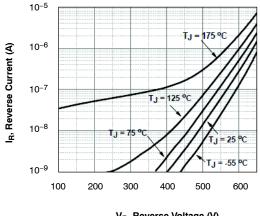
Figure 1. Forward Characteristics











V<sub>R</sub>, Reverse Voltage (V)

Figure 2. Reverse Characteristics

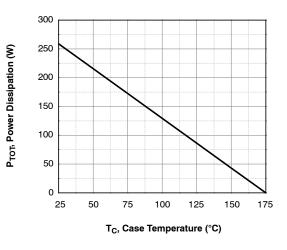


Figure 4. Power Derating

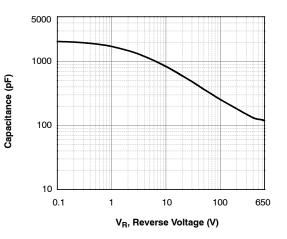
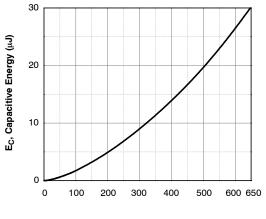


Figure 6. Capacitance vs. Reverse Voltage

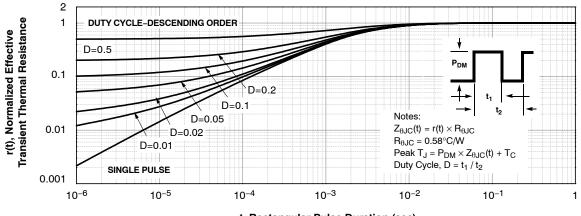
# TYPICAL CHARACTERISTICS (Continued)

(T<sub>J</sub> =  $25^{\circ}C$  unless otherwise noted)



V<sub>R</sub>, Reverse Voltage (V)





t, Rectangular Pulse Duration (sec)

Figure 8. Junction-to-Case Transient Thermal Response Curve

## **TEST CIRCUIT AND WAVEFORMS**

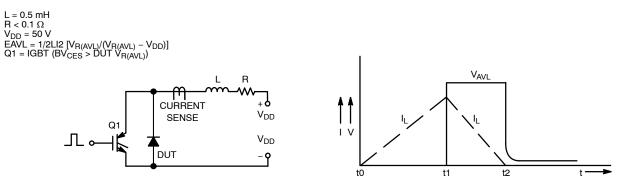


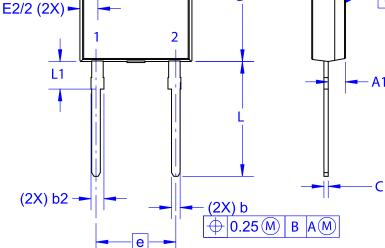
Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

F

А

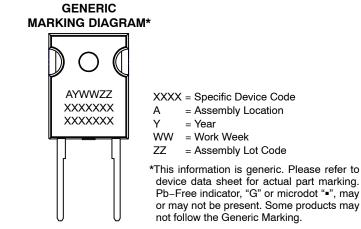
E2

TO-247-2LD CASE 340CL **ISSUE A** DATE 03 DEC 2019 Α ØP -A2 Q S D В E1 1



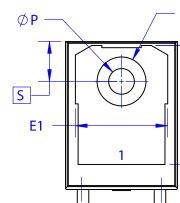
NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 2009. D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.



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DIM	MILLIMETERS				
DIN	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A1	2.29	2.40	2.66		
A2	1.30	1.50	1.70		
b	1.17	1.26	1.35		
b2	1.53	1.65	1.77		
С	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	16.37	16.57	16.77		
D2	0.51	0.93	1.35		
E	15.37	15.62	15.87		
E1	12.81	2	~		
E2	4.96	5.08	5.20		
e	~	11.12	~		
L	15.75	16.00	16.25		
L1	3.69	3.81	3.93		
ØР	3.51	3.58	3.65		
Ø <b>P</b> 1	6.61	6.73	6.85		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

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D2

D1

Ø**P**1

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